

ABSTRACT OF THE DISCLOSURE



162162



G00002

3-5 GROUP COMPOUND SEMICONDUCTOR AND
SEMICONDUCTOR DEVICE

A 3-5 group compound semiconductor comprising a conductive substrate and a device layer of a 3-5 group compound semiconductor formed by epitaxial growth on said conductive substrate, which comprises between said conductive substrate and said device layer a pn laminate structure layer having at least one pn junction comprising a p-type layer having p-type conductivity and an n-type layer having n-type conductivity.

(Figure 1)